CMSL008N03L

30V, 0.6mΩ typ., 400A N-Channel MOSFET

General Description

The CMSL008N03L uses advanced SGT technology to provide excellent RDS(ON).It can be used in a wide variety of applications.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
30V	0.8mΩ	400A

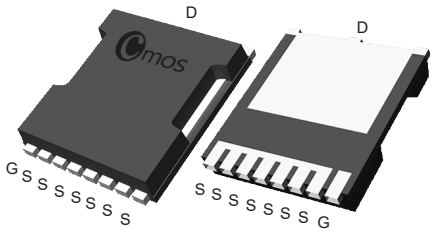
Applications

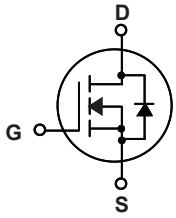
- Motor Driver
- Battery Protection
- Power Distribution

Features

- Low On-Resistance
- 100% avalanche tested
- Surface Mount Package
- RoHS Compliant

TOLL-8 Pin Configuration





TOLL-8
CMSL008N03L

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	400	A
I_D@T_C=100℃	Continuous Drain Current	280	A
I_{DM}	Pulsed Drain Current	1600	A
EAS	Single Pulse Avalanche Energy[1]	1800	mJ
P_D@T_C=25℃	Total Power Dissipation	300	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient[2]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.42	℃/W

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=30A	---	0.6	0.8	mΩ
		V_{GS}=4.5V , I_D=20A	---	0.74	0.95	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS} =0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS} =±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=20A	---	68	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.8	---	Ω
Q_g	Total Gate Charge	I_D=36A V_{DD}=15V V_{GS}=0 to 10V	---	150	---	nC
Q_{gs}	Gate-Source Charge		---	39	---	
Q_{gd}	Gate-Drain Charge		---	12	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD} =15V V_{GS} =10V R_{GEN}= 6Ω , I_D=36A	---	30	---	ns
T_r	Rise Time		---	28	---	
$T_{d(off)}$	Turn-Off Delay Time		---	81	---	
T_f	Fall Time		---	20	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	9800	---	pF
C_{oss}	Output Capacitance		---	2400	---	
C_{rss}	Reverse Transfer Capacitance		---	300	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	400	A
I_{SM}	Pulsed Source Current		---	---	1600	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=30A ,T_J=25℃	---	0.73	1.3	V

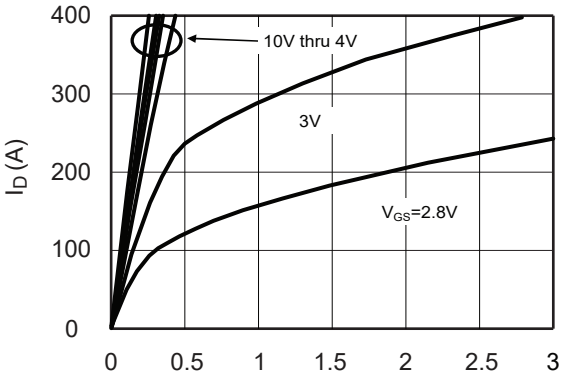
Note :

1.The EAS data shows Max. rating . The test condition is V_{DD}=45V , V_{GS}=10V , L=1mH , I_{AS}=60A.

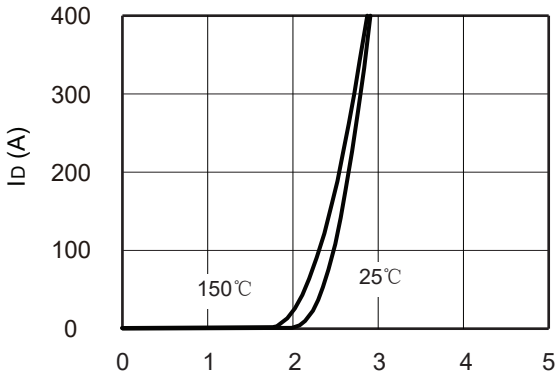
2.Device on 40mm x 40mm x 1.5mm epoxy PCB FR4 with 6 cm^2 (one layer, 70μm thick) copper area for drain connection. PCB is vertical in still air.

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Cmos assumes no liability for customers' product design or applications.
Cmos reserver the right to improve product design ,functions and reliability wihtout notice.Please refer to the latest version of specification.

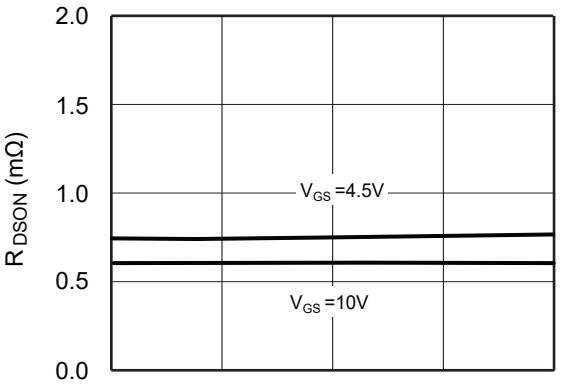
Typical Characteristics



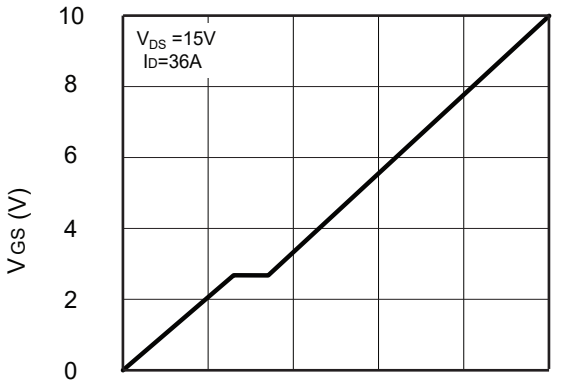
Output Characteristics



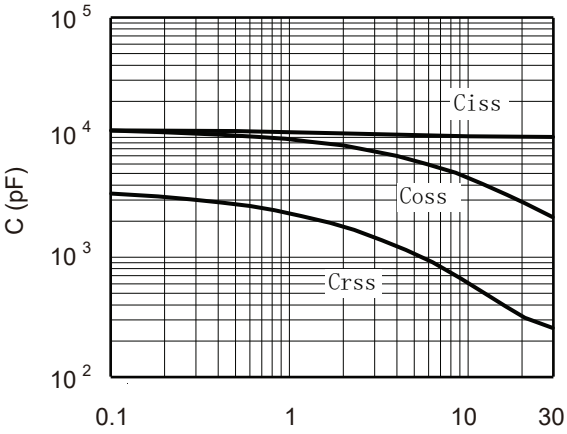
transfer characteristics



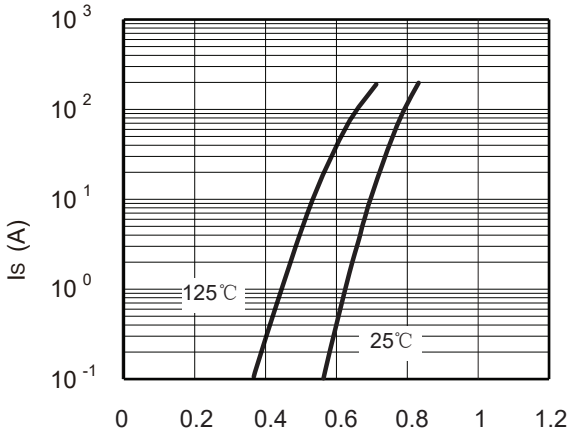
drain-source on-resistance



Gate charge vs gate-source voltage



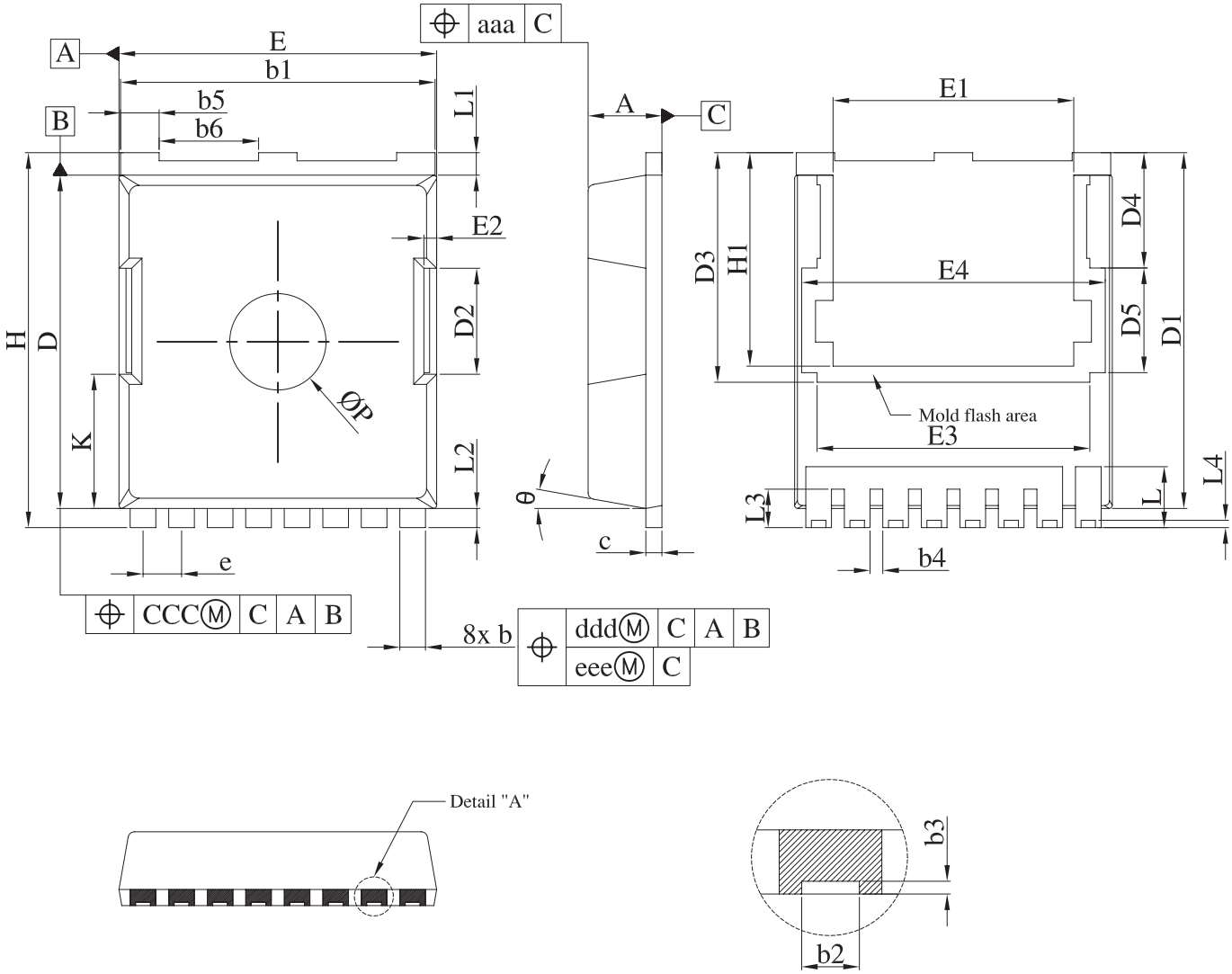
Capacitance Characteristics



Body-Diode Characteristics

Package Dimension

TOLL-8 Unit :mm



SYMBOL		A	b	b1	b2	b3	b4	b5	b6	c	D	D1	D2	D3	D4	D5	e	E	E1
MILLIMETER	MIN.	2.2	0.7	9.7	0.36	0.05	0.3	1.1	3	0.4	10.28	10.98	3.2	7.15	3.59	3.26	1.1	9.8	7.4
	TYP.	2.3	0.8	9.8	0.45	0.1	0.4	1.2	3.1	0.5	10.38	11.08	3.3				1.2	9.9	7.5
	MAX.	2.4	0.9	9.9	0.55	/	0.5	1.3	3.2	0.6	10.55	11.18	3.4				1.3	10	7.6

SYMBOL		E2	E3	E4	H	H1	K	L	L1	L2	L3	L4	P	θ	aaa	ccc	ddd	eee	
MILLIMETER	MIN.	0.3	8.5	9.46	11.5	6.55	4.08	1.6	0.5	0.5	1	0.13	2.85	10° REF	0.2	0.2	0.25	0.2	
	TYP.	0.4			11.68	6.65	4.18	1.9	0.7	0.6	1.2	0.23	3						
	MAX.	0.5			11.85	6.75	4.28	2.1	0.9	0.7	1.3	0.33	3.15						